

IN THE CLAIMS:

1.-35. (Cancelled)

36. (Currently Amended) The semiconductor light emitting device of Claim 55 [[35]], wherein

the multilayer epitaxial structure is formed on the base substrate leaving a space along each edge of a main surface of the base substrate which faces the multilayer epitaxial structure; and

the first through hole and the second through hole are provided in a peripheral portion of the base substrate, the peripheral portion corresponding to the space.

37. (Currently Amended) The semiconductor light emitting device of Claim 55 [[35]], further comprising:

a metal reflective film that is sandwiched between the multilayer epitaxial structure and the base substrate.

38.-45. (Cancelled)

46. (Currently Amended) The semiconductor light emitting device of Claim 55 [[35]], wherein

the first and the second through holes are positioned in a periphery of the base substrate, and

the multilayer epitaxial structure is not positioned on or over the first and second through holes.

47.-51. (Cancelled)

52. (Currently Amended) The semiconductor light emitting device of Claim 55 [[35]], wherein

the phosphor layer covers an entirety of the base substrate, including surrounding edge portions of the base substrate, and

5 a peripheral lateral surface of the base substrate and a peripheral lateral surface of the phosphor layer are a continuous surface.

53. - 54. (Cancelled)

55. (New) A semiconductor light emitting device comprising:

a base substrate made of a highly heat-conductive material; and

5 a pair of power supply terminal thin-film layers, each being provided on different areas of a first main surface of the base substrate, and the pair of power supply terminal thin-film layers being electrically connected to each other via through-holes provided in the base substrate, wherein

a second main surface of the base substrate has provided thereon a semiconductor multilayer epitaxial structure including a first conductive layer, a light emitting layer , and a second conductive layer formed in the stated order,

10 the multilayer epitaxial structure is mounted on the base substrate in such a manner that a last epitaxially-grown layer having a structure characteristic of being grown on a single-crystal substrate different from the base substrate is positioned closer to the base substrate than a portion of a first epitaxially-grown layer,

15 a first electrode thin-film layer is in contact with the first conductive layer,
a second electrode thin-film layer is in contact with the second conductive layer,
a phosphor film covers the semiconductor multilayer epitaxial structure, and
a first thin-film layer and a second thin-film layer electrically connect the first electrode
thin-film layer and the second electrode thin-film layer respectively via the through-holes,
wherein the base substrate is made of one of SiC, AlN, GaN, BN, Si, and sapphire.

56. (New) A semiconductor light emitting device comprising:
a base substrate made of a highly heat-conductive material; and
a pair of power supply terminal thin-film layers, each being provided on different
areas of a first main surface of the base substrate, and the pair of power supply terminal thin-film
5 layers being electrically connected to each other via through-holes provided in the base substrate,
wherein
a second main surface of the base substrate has provided thereon a semiconductor
multilayer epitaxial structure including a first conductive layer, a light emitting layer, and a
second conductive layer formed in the stated order,
10 the multilayer epitaxial structure is mounted on the base substrate in such a
manner that a last epitaxially-grown layer having a structure characteristic of being grown on a
single-crystal substrate different from the base substrate is positioned closer to the base substrate
than a portion of a first epitaxially-grown layer,
a first electrode thin-film layer is in contact with the first conductive layer,
15 a second electrode thin-film layer is in contact with the second conductive layer,
a phosphor film covers the semiconductor multilayer epitaxial structure, and

a first thin-film layer and a second thin-film layer electrically connect the first electrode thin-film layer and the second electrode thin-film layer respectively via the through-holes, wherein the base substrate is made of a highly-resistive semiconductor material.

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57. (New) The semiconductor light emitting device of Claim 56, wherein the multilayer epitaxial structure is formed on the base substrate leaving a space along each edge of a main surface of the base substrate which faces the multilayer epitaxial structure; and

5 the first through hole and the second through hole are provided in a peripheral portion of the base substrate, the peripheral portion corresponding to the space.

58. (New) The semiconductor light emitting device of Claim 56, further comprising: a metal reflective film that is sandwiched between the multilayer epitaxial structure and the base substrate.

59. (New) The semiconductor light emitting device of Claim 56, wherein the first and the second through holes are positioned in a periphery of the base substrate, and the multilayer epitaxial structure is not positioned on or over the first and second through 5 holes.

60. (New) The semiconductor light emitting device of Claim 56, wherein the phosphor layer covers an entirety of the base substrate, including surrounding edge portions of the base substrate, and

a peripheral lateral surface of the base substrate and a peripheral lateral surface of the
5 phosphor layer are a continuous surface.